

ABSTRACT OF THE DISCLOSURE

In a method of forming a silicon-oxide-nitride—oxide-silicon (SONOS) type nonvolatile memory device, a plurality of first gates may be formed on a semiconductor substrate. A plurality of charge storage spacers may be formed on the plurality of first gates so that a given charge storage spacer may be disposed on a sidewall of a given first gate. A plurality of second gates may be disposed on the plurality of first gates so that a given second gate is on a sidewall of a given first gate and covers a given charge storage spacer.